

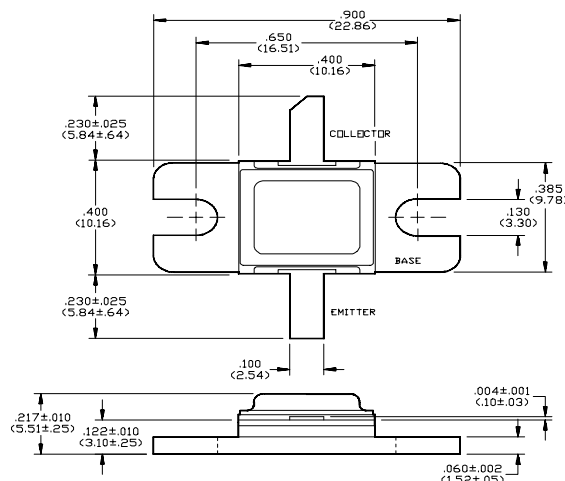
Radar Pulsed Power Transistor - 80 Watts, 1.20-1.40 GHz, 150µs Pulse, 10% Duty



Features

- NPN Silicon Microwave Power Transistor
- Common Base Configuration
- Broadband Class C Operation
- High Efficiency Interdigitated Geometry
- Diffused Emitter Ballasting Resistors
- Gold Metalization System
- Internal Input and Output Impedance Matching
- Hermetic Metal/Ceramic Package

Outline Drawing¹



Notes: (unless otherwise specified)

1. Tolerances are: inches ± .005" (millimeters ± 0.13mm)

Description

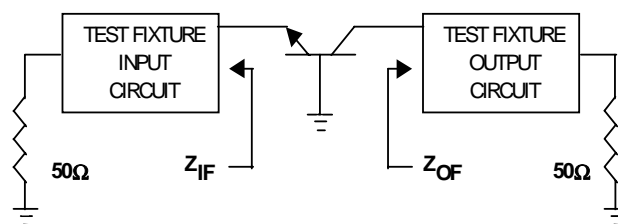
M/A-COM's PH1214-80M is a silicon bipolar NPN power transistor designed for use in L-band, 1.2 - 1.4 GHz pulsed radars such as air traffic control and long-range weather radars. Designed for common-base, class C, broadband pulsed power applications, the PH1214-80M can produce 80 watts of output power with medium pulse length (150 µs) at 10 percent duty cycle. The transistor is housed in a 2-lead, rectangular metal-ceramic flange package, with internal input and output impedance matching networks. Dissued emitter ballast resistors and gold metalization assure ruggedness and long-term reliability. In addition to L-band pulsed radars, this high performance power transistor can also be used in pulsed digital communications systems.

Absolute Maximum Rating at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	70	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	I_C	6.4	A
Total Power Dissipation @ +25°C	P_{TOT}	185	W
Storage Temperature	T_{stg}	-65 to +200	°C
Junction Temperature	T_j	200	°C

Broadband Test Fixture Impedance

F (GHz)	Z_{IF} (Ω)	Z_{OF} (Ω)
1.20	9.4 - j4.5	7.0 - j2.8
1.30	8.3 - j2.8	4.5 - j3.2
1.40	7.9 - j1.3	3.0 - j2.1



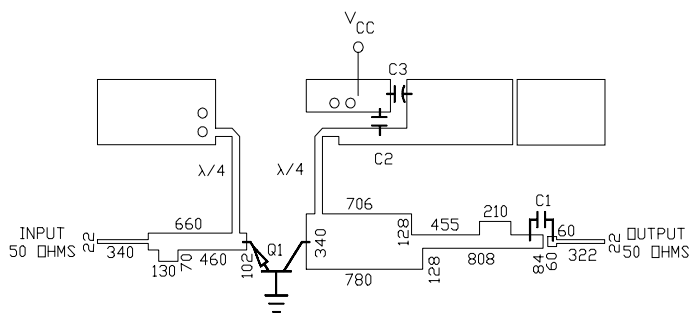
Electrical Specifications at 25°C

Symbol	Parameter	Test Conditions	Min	Max	Units
BV_{CES}	Collector-Emitter Breakdown	$I_C = 35$ mA	70	-	V
I_{CES}	Collector-Emitter Breakdown	$V_{CE} = 40$ V	-	3.5	mA
$R_{TH(JC)}$	Thermal Resistance	$V_{CC} = 40$ V, $P_{in} = 13$ W, $f = 1.2, 1.3, 1.4$ GHz	-	0.80	°C/W
P_O	Output Power	$V_{CC} = 40$ V, $P_{in} = 13$ W, $f = 1.2, 1.3, 1.4$ GHz	80	-	W
G_P	Power Gain	$V_{CC} = 40$ V, $P_{in} = 13$ W, $f = 1.2, 1.3, 1.4$ GHz	7.5	-	dB
η	Collector Efficiency	$V_{CC} = 40$ V, $P_{in} = 13$ W, $f = 1.2, 1.3, 1.4$ GHz	50	-	%
R_L	Input Return Loss	$V_{CC} = 40$ V, $P_{in} = 13$ W, $f = 1.2, 1.3, 1.4$ GHz	9	-	dB
VSWR-T	Load Mismatch Tolerance	$V_{CC} = 40$ V, $P_{in} = 13$ W, $f = 1.2, 1.3, 1.4$ GHz	-	3:1	-
VSWR-S	Load Mismatch Stability	$V_{CC} = 40$ V, $P_{in} = 13$ W, $f = 1.2, 1.3, 1.4$ GHz	-	1.5:1	-

V2.00

Test Fixture Electrical Schematic¹

Top View



PH1214-80M

Note:

1. Dimensions are in mils.

Electrical Schematic Parts List

C1, C2	100 pF ATC size A
C3	50 uF 50 Volts
Q1	PH1214-80M
Board Type	Rogers 6010.5 .025" Thick, E _R = 10.5

